# **SiT8920B**

-55°C to +125°C Oscillator



## **Features**

- Frequencies between 1 MHz and 110 MHz accurate to 6 decimal places
- Operating temperature from -55°C to 125°C
- Supply voltage of 1.8 V or 2.5 V to 3.3 V
- Excellent total frequency stability as low as ±20 ppm
- Low power consumption of 3.5 mA typical at 1.8 V
- LVCMOS/LVTTL compatible output
- Industry-standard packages: 2.0 x 1.6, 2.5 x 2.0, 3.2 x 2.5, 5.0 x 3.2, 7.0 x 5.0 mm x mm
- Instant samples with Time Machine II and field programmable oscillators
- RoHS and REACH compliant, Pb-free, Halogen-free and Antimony-free

## **Applications**

 Ruggedized equipment in harsh operating environment Related products for automotive applications.

For aerospace and defense applications SiTime recommends using only Endura™ SiT8944.





SiTimeDirect





## **Table 1. Electrical Characteristics**

All Min and Max limits are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at 25°C and nominal supply voltage.

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition
			Fi	requency R	ange	
Output Frequency Range	f	1	_	110	MHz	Refer to Table 13 for the exact list of supported frequencies list of supported frequencies
			Frequen	cy Stability	and Aging	g
Frequency Stability	F_stab	-20	-	+20	ppm	Inclusive of Initial tolerance at 25°C, 1st year aging at 25°C,
		-25	_	+25	ppm	and variations over operating temperature, rated power supply voltage and load (15 pF ±10%).
		-30	-	+30	ppm	Supply Voltage and load (15 pt ±10%).
		-50	-	+50	ppm	
			Operation	ng Tempera	ture Rang	e
Operating Temperature Range	T_use	-55	-	+125	°C	
		Sı	ipply Voltag	e and Curr	ent Consu	mption
Supply Voltage	Vdd	1.62	1.8	1.98	V	
		2.25	2.5	2.75	V	
		2.52	2.8	3.08	V	
		2.7	3.0	3.3	V	
		2.97	3.3	3.63	V	
		2.25	-	3.63	V	
Current Consumption	ldd	-	3.8	4.7	mA	No load condition, $f = 20$ MHz, $Vdd = 2.8$ V, $3.0$ V or $3.3$ V
		-	3.6	4.5	mA	No load condition, f = 20 MHz, Vdd = 2.5 V
		-	3.5	4.5	mA	No load condition, f = 20 MHz, Vdd = 1.8 V
OE Disable Current	l_od	-	_	4.5	mA	Vdd = 2.5 V to 3.3 V, OE = Low, Output in high Z state.
		-	_	4.3	mA	Vdd = 1.8 V, OE = Low, Output in high Z state.
Standby Current	I_std	1	2.6	8.5	μА	$Vdd = 2.8 V to 3.3 V, \overline{ST} = Low, Output is weakly pulled down$
		-	1.4	5.5	μΑ	Vdd = 2.5 V, $\overline{ST}$ = Low, Output is weakly pulled down
		-	0.6	4.0	μА	Vdd = 1.8 V, $\overline{ST}$ = Low, Output is weakly pulled down
			LVCMOS	Output Ch	aracteristic	cs
Duty Cycle	DC	45	_	55	%	All Vdds
Rise/Fall Time	Tr, Tf	_	1.0	2.0	ns	Vdd = 2.5 V, 2.8 V, 3.0 V or 3.3 V, 20% - 80%
		-	1.3	2.5	ns	Vdd = 1.8 V, 20% - 80%
		ı	1.0	3	ns	Vdd = 2.25 V - 3.63 V, 20% - 80%
Output High Voltage	VOH	90%	-	-	Vdd	IOH = -4 mA (Vdd = 3.0 V or 3.3 V) IOH = -3 mA (Vdd = 2.8 V or 2.5 V) IOH = -2 mA (Vdd = 1.8 V)
Output Low Voltage	VOL	-	_	10%	Vdd	IOL = 4 mA (Vdd = 3.0 V or 3.3 V) IOL = 3 mA (Vdd = 2.8 V or 2.5 V) IOL = 2 mA (Vdd = 1.8 V)



**Table 1. Electrical Characteristics (continued)** 

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition				
			Inp	ut Characte	ristics					
Input High Voltage	VIH	70%	-	-	Vdd	Pin 1, OE or ST				
Input Low Voltage	VIL	-	-	30%	Vdd	Pin 1, OE or ST				
Input Pull-up Impedance	Z_in	50	87	150	kΩ	Pin 1, OE logic high or logic low, or ST logic high				
		2	-	-	ΜΩ	Pin 1, ST logic low				
Startup and Resume Timing										
Startup Time	T_start	-	-	5	ms	Measured from the time Vdd reaches its rated minimum value				
Enable/Disable Time	T_oe	-	-	130	ns	f = 110 MHz. For other frequencies, T_oe = 100 ns + 3 * clock periods				
Resume Time	T_resume	-	-	5	ms	Measured from the time ST pin crosses 50% threshold				
				Jitter						
RMS Period Jitter	T_jitt	_	1.6	2.5	ps	f = 75 MHz, Vdd = 2.5 V, 2.8 V, 3.0 V or 3.3 V				
		_	1.9	3	ps	f = 75 MHz, Vdd = 1.8 V				
Peak-to-peak Period Jitter	T_pk	_	12	20	ps	f = 75 MHz, Vdd = 2.5 V, 2.8 V, 3.0 V or 3.3 V				
		_	14	25	ps	f = 75 MHz, Vdd = 1.8 V				
RMS Phase Jitter (random)	T_phj	_	0.5	0.8	ps	f = 75 MHz, Integration bandwidth = 900 kHz to 7.5 MHz				
		-	1.3	2	ps	f = 75 MHz, Integration bandwidth = 12 kHz to 20 MHz				

## **Table 2. Pin Description**

Pin	Symbol	Functionality					
		Output Enable	H <sup>[1]</sup> : specified frequency output L: output is high impedance. Only output driver is disabled.				
1	OE/ST/NC	Standby	H <sup>[1]</sup> : specified frequency output L: output is low (weak pull down). Device goes to sleep mode. Supply current reduces to I_std.				
		No Connect	Any voltage between 0 and Vdd or Open <sup>[1]</sup> : Specified frequency output. Pin 1 has no function.				
2	GND	Power	Electrical ground				
3	OUT	Output	Oscillator output				
4	VDD	Power	Power supply voltage <sup>[2]</sup>				

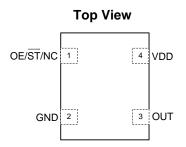


Figure 1. Pin Assignments

- 1. In OE or  $\overline{ST}$  mode, a pull-up resistor of 10 kΩ or less is recommended if pin 1 is not externally driven. If pin 1 needs to be left floating, use the NC option.
- 2. A capacitor of value 0.1 µF or higher between Vdd and GND is required.



## **Table 3. Absolute Maximum Limits**

Attempted operation outside the absolute maximum ratings of the part may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
VDD	-0.5	4	V
Electrostatic Discharge	-	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	-	260	°C
Junction Temperature <sup>[3]</sup>	-	150	°C

### Note:

### Table 4. Thermal Consideration<sup>[4]</sup>

Package	θJA, 4 Layer Board (°C/W)	θJA, 2 Layer Board (°C/W)	θJC, Bottom (°C/W)
7050	142	273	30
5032	97	199	24
3225	109	212	27
2520	117	222	26
2016	152	252	36

#### Note:

## Table 5. Maximum Operating Junction Temperature<sup>[5]</sup>

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
125°C	135°C

#### Note:

5. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

### **Table 6. Environmental Compliance**

<u> </u>	
Parameter	Condition/Test Method
Mechanical Shock	MIL-STD-883F, Method2002
Mechanical Vibration	MIL-STD-883F, Method2007
Temperature Cycle	JESD22, Method A104
Solderability	MIL-STD-883F, Method2003
Moisture Sensitivity Level	MSL1 @ 260°C

<sup>3.</sup> Exceeding this temperature for extended period of time may damage the device.

<sup>4.</sup> Refer to JESD51-7 for  $\theta$ JA and  $\theta$ JC definitions, and reference layout used to determine the  $\theta$ JA and  $\theta$ JC values in the above table.



## **Test Circuit and Waveform**

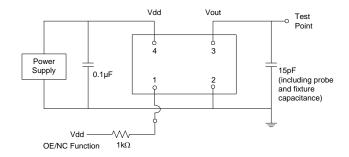
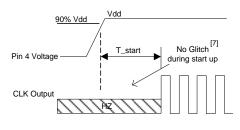


Figure 2. Test Circuit<sup>[6]</sup>

## Notes:

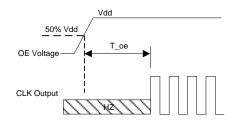
6. Duty Cycle is computed as Duty Cycle = TH/Period.

# **Timing Diagram**



T\_start: Time to start from power-off

Figure 4. Startup Timing (OE/ST Mode)



T\_oe: Time to re-enable the clock output

Figure 6. OE Enable Timing (OE Mode Only)

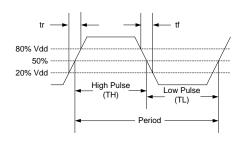
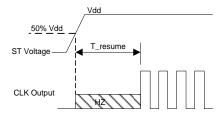
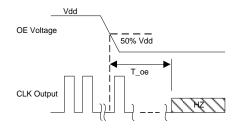


Figure 3. Waveform<sup>[6]</sup>



T\_resume: Time to resume from ST

Figure 5. Standby Resume Timing (ST Mode Only)



T\_oe: Time to put the output in High Z mode

Figure 7. OE Disable Timing (OE Mode Only)

#### Note:

7. SiT8920 has "no runt" pulses and "no glitch" output during startup or resume.



## Performance Plots[8]

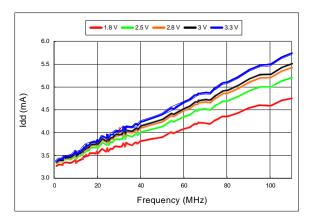


Figure 8. Idd vs Frequency

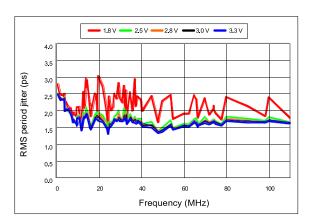


Figure 10. RMS Period Jitter vs Frequency

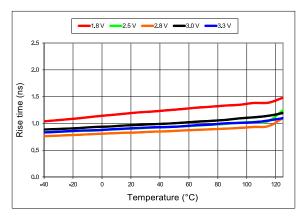


Figure 12. 20%-80% Rise Time vs Temperature

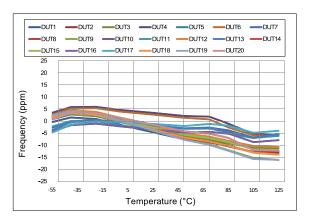


Figure 9. Frequency vs Temperature

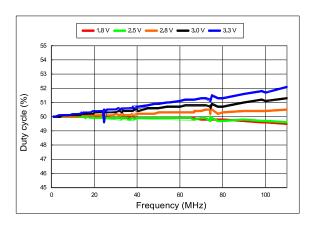


Figure 11. Duty Cycle vs Frequency

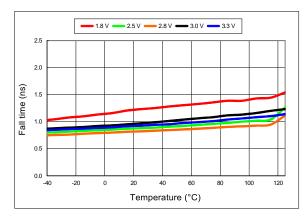
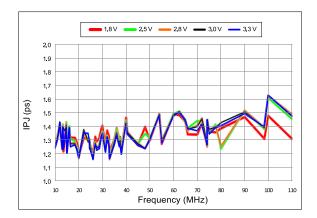
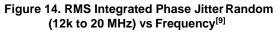


Figure 13. 20%-80% Fall Time vs Temperature



## Performance Plots[8]





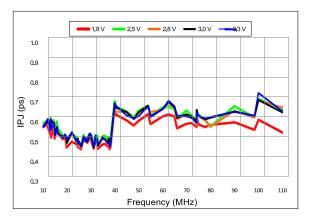


Figure 15. RMS Integrated Phase Jitter Random (900 kHz to 20 MHz) vs Frequency<sup>[9]</sup>

- 8. All plots are measured with 15 pF load at room temperature, unless otherwise stated.
- 9. Phase noise plots are measured with Agilent E5052B signal source analyzer. Integration range is 12 kHz to 5 MHz for carrier f requencies up to 40 MHz.



## **Programmable Drive Strength**

The SiT8920 includes a programmable drive strength feature to provide a simple, flexible tool to optimize the clock rise/fall time for specific applications. Benefits from the programmable drive strength feature are:

- Improves system radiated electromagnetic interference (EMI) by slowing down the clock rise/fall time
- Improves the downstream clock receiver's (RX) jitter by decreasing (speeding up) the clock rise/fall time.
- Ability to drive large capacitive loads while maintaining

full swing with sharp edge rates.

For more detailed information about rise/fall time control and drive strength selection, see the SiTime Application Notes section.

## **EMI Reduction by Slowing Rise/Fall Time**

Figure 16 shows the harmonic power reduction as the rise/fall times are increased (slowed down). The rise/fall times are expressed as a ratio of the clock period. For the ratio of 0.05, the signal is very close to a square wave. For the ratio of 0.45, the rise/fall times are very close to near-triangular waveform. These results, for example, show that the 11th clock harmonic can be reduced by 35 dB if the rise/fall edge is increased from 5% of the period to 45% of the period.

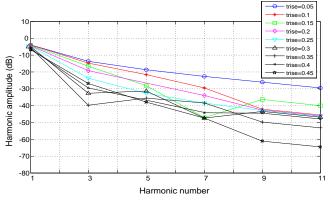


Figure 16. Harmonic EMI reduction as a Function of Slower Rise/Fall Time

### Jitter Reduction with Faster Rise/Fall Time

Power supply noise can be a source of jitter for the downstream chipset. One way to reduce this jitter is to speed up the rise/fall time of the input clock. Some chipsets may also require faster rise/fall time in order to reduce their sensitivity to this type of jitter. Refer to the Rise/Fall Time Tables (Table 7 to 11) to determine the proper drive strength.

## **High Output Load Capability**

The rise/fall time of the input clock varies as a function of the actual capacitive load the clock drives. At any given drive strength, the rise/fall time becomes slower as the output load increases. As an example, for a 3.3 V SiT8920 device with default drive strength setting, the typical rise/fall time is 1ns for 15 pF output load. The typical rise/fall time slows down to

2.6 ns when the output load increases to 45 pF. One can choose to speed up the rise/fall time to 1.83 ns by then increasing the drive strength setting on the SiT8920.

The SiT8920 can support up to 60 pF or higher in maximum capacitive loads with drive strength settings. Refer to the Rise/Tall Time Tables (Tables 7 to 11) to determine the proper drive strength for the desired combination of output load vs. rise/fall time.

## SiT8920 Drive Strength Selection

Tables 7 through 11 define the rise/fall time for a given capacitive load and supply voltage.

- 1. Select the table that matches the SiT8920 nominal supply voltage (1.8 V, 2.5 V, 2.8 V, 3.0 V, 3.3 V).
- 2. Select the capacitive load column that matches the application requirement (5 pF to 60 pF)
- Under the capacitive load column, select the desired rise/fall times.
- **4.** The left-most column represents the part number code for the corresponding drive strength.
- Add the drive strength code to the part number for ordering purposes.

## **Calculating Maximum Frequency**

Based on the rise and fall time data given in Tables 7 through 11, the maximum frequency the oscillator can operate with guaranteed full swing of the output voltage over temperature as follows:

Max Frequency = 
$$\frac{1}{5 \times T \text{ rf}_20/80}$$

where  $Trf_20/80$  is the typical value for 20%-80% rise/fall time.

### Example 1

Calculate fMAX for the following condition:

- Vdd = 1.8 V (Table 7)
- Capacitive Load: 30 pF
- Desired Tr/f time = 3 ns (rise/fall time part number code = E)

Part number for the above example:

SiT8920BME12-18E-66.666660



Drive strength code is inserted here. Default setting is "-"



# Rise/Fall Time (20% to 80%) vs C<sub>LOAD</sub> Tables

Table 7. Vdd = 1.8 V Rise/Fall Times for Specific  $C_{LOAD}$ 

Rise/Fall Time Typ (ns)									
Drive Strength \ C <sub>LOAD</sub>	5 pF	15 pF	30 pF	45 pF	60 pF				
L	6.16	11.61	22.00	31.27	39.91				
Α	3.19	6.35	11.00	16.01	21.52				
R	2.11	4.31	7.65	10.77	14.47				
В	1.65	3.23	5.79	8.18	11.08				
T	0.93	1.91	3.32	4.66	6.48				
E	0.78	1.66	2.94	4.09	5.74				
U	0.70	1.48	2.64	3.68	5.09				
F or "-": default	0.65	1.30	2.40	3.35	4.56				

Table 8. Vdd = 2.8 V Rise/Fall Times for Specific C<sub>LOAD</sub>

Rise/Fall Time Typ (ns)								
Drive Strength \ C <sub>LOAD</sub>	5 pF	15 pF	30 pF	45 pF	60 pF			
L	3.77	7.54	12.28	19.57	25.27			
Α	1.94	3.90	7.03	10.24	13.34			
R	1.29	2.57	4.72	7.01	9.06			
В	0.97	2.00	3.54	5.43	6.93			
Т	0.55	1.12	2.08	3.22	4.08			
E or "-": default	0.44	1.00	1.83	2.82	3.67			
U	0.34	0.88	1.64	2.52	3.30			
F	0.29	0.81	1.48	2.29	2.99			

Table 11. Vdd = 3.3 V Rise/Fall Times for Specific  $C_{LOAD}$ 

Rise/Fall Time Typ (ns)								
Drive Strength \ C <sub>LOAD</sub>	5 pF	15 pF	30 pF	45 pF	60 pF			
L	3.39	6.88	11.63	17.56	23.59			
Α	1.74	3.50	6.38	8.98	12.19			
R	1.16	2.33	4.29	6.04	8.34			
В	0.81	1.82	3.22	4.52	6.33			
T or "-": default	0.46	1.00	1.86	2.60	3.84			
E	0.33	0.87	1.64	2.30	3.35			
U	0.28	0.79	1.46	2.05	2.93			
F	0.25	0.72	1.31	1.83	2.61			

Table 9. Vdd = 2.5 V Rise/Fall Times for Specific  $C_{LOAD}$ 

Rise/Fall Time Typ (ns)								
Drive Strength \ C <sub>LOAD</sub>	5 pF	15 pF	30 pF	45 pF	60 pF			
L	4.13	8.25	12.82	21.45	27.79			
Α	2.11	4.27	7.64	11.20	14.49			
R	1.45	2.81	5.16	7.65	9.88			
В	1.09	2.20	3.88	5.86	7.57			
T	0.62	1.28	2.27	3.51	4.45			
E or "-": default	0.54	1.00	2.01	3.10	4.01			
U	0.43	0.96	1.81	2.79	3.65			
F	0.34	0.88	1.64	2.54	3.32			

Table 10. Vdd = 3.0 V Rise/Fall Times for Specific  $C_{\text{LOAD}}$ 

Rise/Fall Time Typ (ns)								
Drive Strength \ C <sub>LOAD</sub>	5 pF	15 pF	30 pF	45 pF	60 pF			
L	3.60	7.21	11.97	18.74	24.30			
Α	1.84	3.71	6.72	9.86	12.68			
R	1.22	2.46	4.54	6.76	8.62			
В	0.89	1.92	3.39	5.20	6.64			
T or "-": default	0.51	1.00	1.97	3.07	3.90			
E	0.38	0.92	1.72	2.71	3.51			
U	0.30	0.83	1.55	2.40	3.13			
F	0.27	0.76	1.39	2.16	2.85			



# Pin 1 Configuration Options (OE, ST, or NC)

Pin 1 of the SiT8920 can be factory-programmed to support three modes: Output enable (OE), standby (ST) or No Connect (NC). These modes can also be programmed with the Time Machine using field programmable devices.

## **Output Enable (OE) Mode**

In the OE mode, applying logic Low to the OE pin only disables the output driver and puts it in Hi-Z mode. The core of the device continues to operate normally. Power consumption is reduced due to the inactivity of the output. When the OE pin is pulled High, the output is typically enabled in  $<1\mu$ s.

## Standby (ST) Mode

In the  $\overline{ST}$  mode, a device enters into the standby mode when Pin 1 pulled Low. All internal circuits of the device are turned off. The current is reduced to a standby current, typically in the range of a few  $\mu A$ . When  $\overline{ST}$  is pulled High, the device goes through the "resume" process, which can take up to 5 ms.

## No Connect (NC) Mode

In the NC mode, the device always operates in its normal mode and output the specified frequency regardless of the logic level on pin 1.

Table 12 below summarizes the key relevant parameters in the operation of the device in OE,  $\overline{ST}$ , or NC mode.

Table 12. OE vs. ST vs. NC

	OE	ST	NC
Active current 20 MHz (max, 1.8 V)	4.5 mA	4.5 mA	4.5 mA
OE disable current (max. 1.8 V)	4.3 mA	N/A	N/A
Standby current (typical 1.8 V)	N/A	0.6 uA	N/A
OE enable time at 110 MHz (max)	130 ns	N/A	N/A
Resume time from standby (max, all frequency)	N/A	5 ms	N/A
Output driver in OE disable/standby mode	High Z	weak pull-down	N/A

### **Output on Startup and Resume**

The SiT8920 comes with gated output. Its clock output is accurate to the rated frequency stability within the first pulse from initial device startup or resume from the standby mode.

In addition, the SiT8920 has NO RUNT, NO GLITCH output during startup or resume as shown in the waveform captures in Figure 17 and Figure 18.

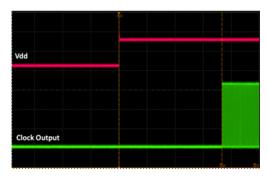


Figure 17. Startup Waveform vs. Vdd

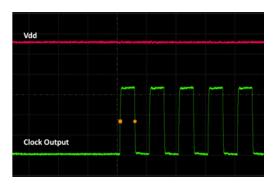


Figure 18. Startup Waveform vs. Vdd (Zoomed-in View of Figure 17)

# Instant Samples with Time Machine and Field Programmable Oscillators

SiTime supports a field programmable version of the SiT8920 high temperature oscillator for fast prototyping and real time customization of features. The field programmable devices (FP devices) are available for all five standard SiT8920 package sizes and can be configured to one's exact specification using the Time Machine II, an USB powered MEMS oscillator programmer.

# **Customizable Features of the SiT8920 FP Devices Include**

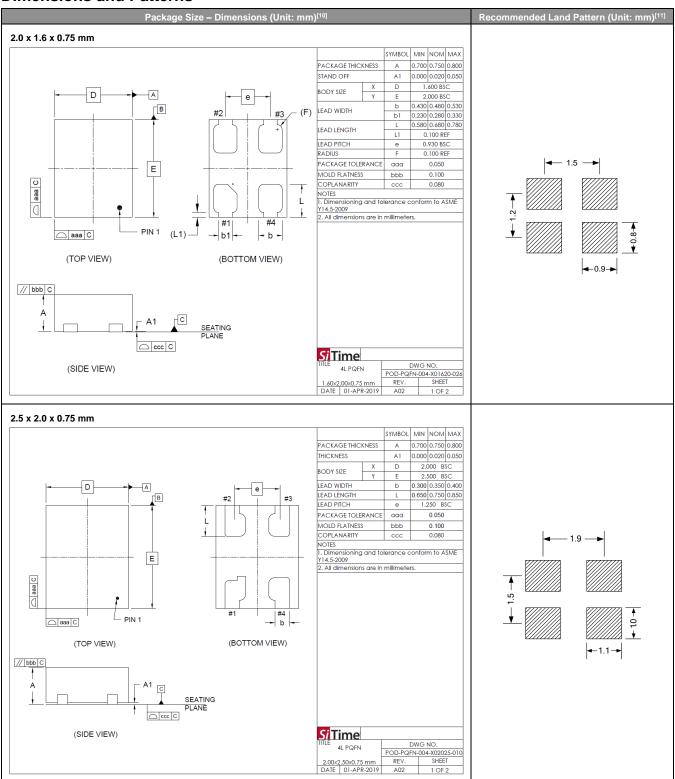
- Frequencies between 1 110 MHz
- Four frequency stability options, ±20 ppm, ±25 ppm, ±30 ppm, ±50 ppm
- Six supply voltage options, 1.8 V, 2.5 V, 2.8 V, 3.0 V, 3.3 V and 2.25 to 3.63 V continuous
- Output drive strength

For more information regarding SiTime's field programmable solutions, visit Time Machine II and Field Programmable devices.

SiT8920 is factory-programmed per customer ordering codes for volume delivery.

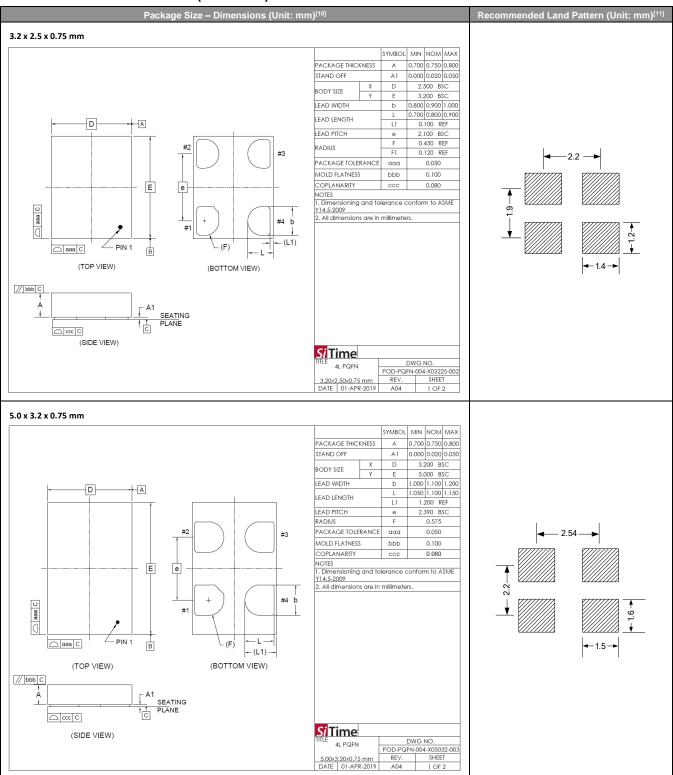


## **Dimensions and Patterns**



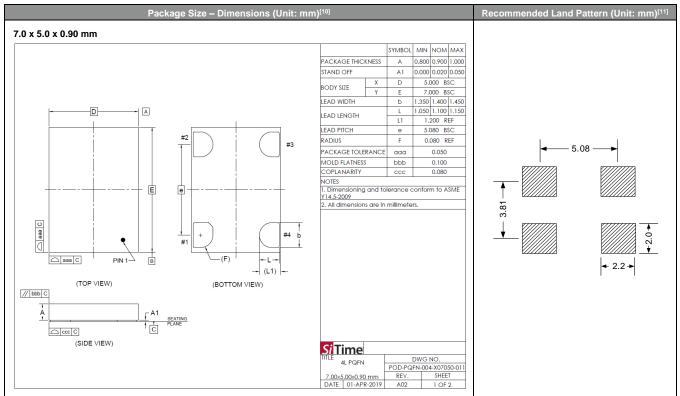


## **Dimensions and Patterns (continued)**





## **Dimensions and Patterns (continued)**



- 10. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the as sembly location of the device.
- 11. A capacitor of value 0.1  $\mu\text{F}$  or higher between Vdd and GND is required.



## **Ordering Information**

The Part No. Guide is for reference only. To customize and build an exact part number, use the SiTime Part Number Generator.

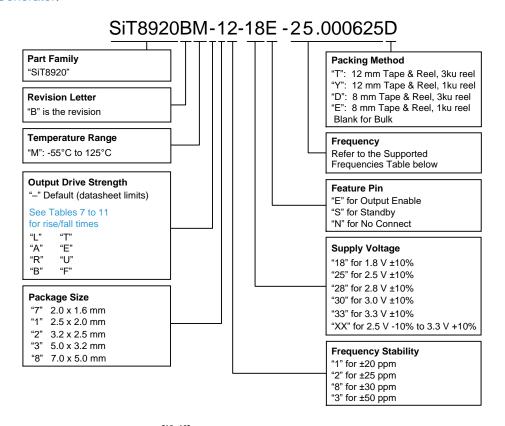


Table 13. List of Supported Frequencies<sup>[12, 13]</sup>

Frequency Range (-55 to +125°C)			
Min.	Max.		
1.000000 MHz	61.222999 MHz		
61.674001 MHz	69.239999 MHz		
70.827001 MHz	78.714999 MHz		
79.561001 MHz	80.159999 MHz		
80.174001 MHz	80.779999 MHz		
82.632001 MHz	91.833999 MHz		
95.474001 MHz	96.191999 MHz		
96.209001 MHz	96.935999 MHz		
99.158001 MHz	110.000000 MHz		

- 12. Any frequency within the min and max values in the above table are supported with 6 decimal places of accuracy.
- 13. Please contact SiTime for frequencies that are not listed in the tables above.

Table 14. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	16 mm T&R (3ku)	16 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	8 mm T&R (3ku)	8 mm T&R (1ku)
2.0 x 1.6	-	-	-	-	D	Е
2.5 x 2.0	-	-	-	-	D	Е
3.2 x 2.5	-	-	-	-	D	Е
5.0 x 3.2	-	-	Т	Υ	-	-
7.0 x 5.0	Т	Υ	-	-	-	-



## **Table 15. Additional Information**

Document	Description	Download Link	
Time Machine II	MEMS oscillator programmer	http://www.sitime.com/support/time-machine-oscillator-programmer	
Field Programmable Oscillators	Devices that can be programmable in the field by Time Machine II	http://www.sitime.com/products/field-programmable-oscillators	
Manufacturing Notes	Tape & Reel dimension, reflow profile and other manufacturing related info	http://https://www.sitime.com/support/resource-library/manufacturing-notes- sitime-products	
Qualification Reports	RoHS report, reliability reports, composition reports	http://www.sitime.com/support/quality-and-reliability	
Performance Reports  Additional performance data such as phase noise, current consumption and jitter for selected frequencies		http://www.sitime.com/support/performance-measurement-report	
Termination Techniques	Termination design recommendations	http://www.sitime.com/support/application-notes	
Layout Techniques Layout recommendations		http://www.sitime.com/support/application-notes	

## **Table 16. Revision History**

Version	Release Date	Change Summary
1.0	7-May-2015	Final production release
1.01	2-Jan-2017	Added 16 mm T&R information to Table 14 Revised 12 mm T&R information to Table 14
1.02	15-Jun-2021	Updated logo and company address, other page layout changes Updated Dimensions and Patterns package drawings
1.03	1-Jan-2023	Updated company disclaimer, links, references and icons

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For aerospace and defense applications, SiTime recommends using only  ${\tt Endura^{TM}}$  ruggedized products.

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# **Supplemental Information**

The Supplemental Information section is not part of the datasheet and is for informational purposes only.



## **Best Reliability**

Silicon is inherently more reliable than quartz. Unlike quartz suppliers, SiTime has in-house MEMS and analog CMOS expertise, which allows SiTime to develop the most reliable products. Figure 1 shows a comparison with quartz technology.

## Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal® process, which eliminates foreign particles and improves long term aging and reliability
- World-class MEMS and CMOS design expertise

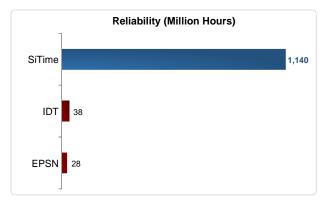


Figure 1. Reliability Comparison<sup>[1]</sup>

### **Best Aging**

Unlike quartz, MEMS oscillators have excellent long term aging performance which is why every new SiTime product specifies 10-year aging. A comparison is shown in Figure 2.

## Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal® process, which eliminates foreign particles and improves long term aging and reliability
- Inherently better immunity of electrostatically driven MEMS resonator

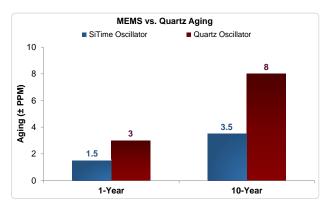


Figure 2. Aging Comparison<sup>[2]</sup>

## **Best Electro Magnetic Susceptibility (EMS)**

SiTime's oscillators in plastic packages are up to 54 times more immune to external electromagnetic fields than quartz oscillators as shown in Figure 3.

## Why is SiTime Best in Class:

- Internal differential architecture for best common mode noise rejection
- Electrostatically driven MEMS resonator is more immune to EMS

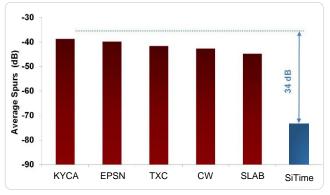


Figure 3. Electro Magnetic Susceptibility (EMS)[3]

## **Best Power Supply Noise Rejection**

SiTime's MEMS oscillators are more resilient against noise on the power supply. A comparison is shown in Figure 4.

### Why is SiTime Best in Class:

- On-chip regulators and internal differential architecture for common mode noise rejection
- MEMS resonator is paired with advanced analog CMOS IC

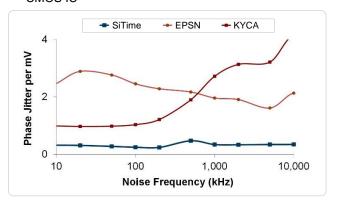


Figure 4. Power Supply Noise Rejection<sup>[4]</sup>



## **Best Vibration Robustness**

High-vibration environments are all around us. All electronics, from handheld devices to enterprise servers and storage systems are subject to vibration. Figure 5 shows a comparison of vibration robustness.

## Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than quartz
- Center-anchored MEMS resonator is the most robust design

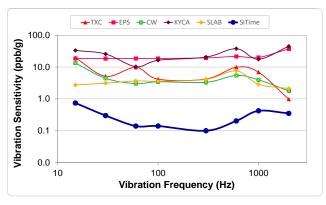


Figure 19. Vibration Robustness<sup>[5]</sup>

### Figure labels:

- TXC = TXC
- Epson = EPSN
- Connor Winfield = CW
- Kyocera = KYCA
- SiLabs = SLAB
- SiTime = EpiSeal MEMS

## **Best Shock Robustness**

SiTime's oscillators can withstand at least 50,000 g shock. They all maintain their electrical performance in operation during shock events. A comparison with quartz devices is shown in Figure 6.

## Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than quartz
- Center-anchored MEMS resonator is the most robust design

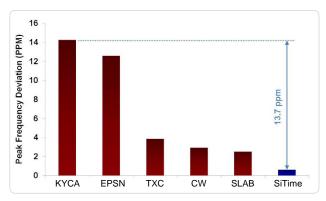


Figure 20. Shock Robustness<sup>[6]</sup>

# **Silicon MEMS Outperforms Quartz**



#### Notes:

- 1. Data source: Reliability documents of named companies.
- 2. Data source: SiTime and quartz oscillator devices datasheets.
- 3. Test conditions for Electro Magnetic Susceptibility (EMS):
  - According to IEC EN61000-4.3 (Electromagnetic compatibility standard)
  - Field strength: 3V/m
  - Radiated signal modulation: AM 1 kHz at 80% depth
     Carrier frequency scan: 80 MHz 1 GHz in 1% steps
  - Antenna polarization: Vertical
  - DUT position: Center aligned to antenna

### Devices used in this test:

Label	Manufacturer	Part Number	Technology
EpiSeal MEMS	SiTime	SiT9120AC-1D2-33E156.250000	MEMS + PLL
EPSN	Epson	EG-2102CA156.2500M-PHPAL3	Quartz, SAW
TXC	TXC	BB-156.250MBE-T	Quartz, 3 <sup>rd</sup> Overtone
CW	Conner Winfield	P123-156.25M	Quartz, 3 <sup>rd</sup> Overtone
KYCA	AVX Kyocera	KC7050T156.250P30E00	Quartz, SAW
SLAB	SiLab	590AB-BDG	Quartz, 3 <sup>rd</sup> Overtone + PLL

4. 50 mV pk-pk Sinusoidal voltage.

### Devices used in this test:

Label	Manufacturer	Part Number	Technology
EpiSeal MEMS	SiTime	SiT8208AI-33-33E-25.000000	MEMS + PLL
NDK	NDK	NZ2523SB-25.6M	Quartz
KYCA	AVX Kyocera	KC2016B25M0C1GE00	Quartz
EPSN	Epson	SG-310SCF-25M0-MB3	Quartz

5. Devices used in this test:

same as EMS test stated in Note 3.

- 6. Test conditions for shock test:
  - MIL-STD-883F Method 2002
  - Condition A: half sine wave shock pulse, 500-g, 1ms
  - Continuous frequency measurement in 100 µs gate time for 10 seconds

### Devices used in this test:

same as EMS test stated in Note 3.

 $7. \ \ \, \text{Additional data, including setup and detailed results, is available upon request to qualified customer. Please contact <math display="block"> \frac{\text{productsupport@sitime.com.}}{\text{productsupport@sitime.com.}}$